



N-CHANNEAL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	RDS(ON) Max	I _{D MAX} Ta = +25°C
	$29m\Omega @ V_{GS} = 4.5V$	5.6A
12V	$34m\Omega @ V_{GS} = 2.5V$	5.1A
1∠V	44mΩ @ V _{GS} = 1.8V	4.5A
	65mΩ @ V _{GS} = 1.5V	3.7A

Description

This MOSFET has been designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- **Power Management Functions**
- Portable Power Adaptors

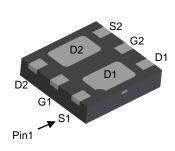
Features

- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

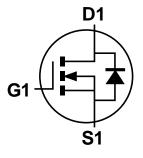
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4)
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

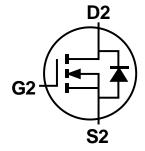
U-DFN2020-6 (Type B)



Bottom View



Q1 N-CHANNEL MOSFET



Q2 N-CHANNEL MOSFET

Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN1029UFDB -7	U-DFN2020-6 (Type B)	3000/Tape & Reel
DMN1029UFDB -13	U-DFN2020-6 (Type B)	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



Marking Information

Site 1



D5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Date Odde Ney												
Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	С		Н		J	K	L	М	N	0	Р	R
		1		I								
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



D5 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = week 27; z represents week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Kev

Date Code Hoy											
Year	2015	 2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	5	 0	1	2	3	4	5	6	7	8	9

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	X	Υ	Z



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	12	V	
Gate-Source Voltage			V _{GSS}	±8	V
State T _A		$T_A = +25$ °C $T_A = +70$ °C	lο	5.6 4.4	А
Continuous Drain Current (Note 5) V _{GS} = 4.5V	t < 5s	$T_A = +25$ °C $T_A = +70$ °C	lο	7.2 5.8	А
Maximum Continuous Body Diode Forward Curre	ent (Note 5)		Is	1	Α
Pulsed Drain Current (10μs Pulse, Duty Cycle =	Ірм	20	Α		
Avalanche Current (L = 0.1mH)		I _{AS}	15	А	
Avalanche Energy (L = 0.1mH)			Eas	12	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit		
Total Dower Dissipation (Note 5)	Steady State	ק	1.4	W	
Total Power Dissipation (Note 5)	t < 5s	P_D	2.2	VV	
Thermal Desigtance Junction to Ambient (Note 5)	Steady State	7	91		
Thermal Resistance, Junction to Ambient (Note 5)	t < 5s	$R_{\theta JA}$	55	°C/W	
Thermal Resistance, Junction to Case	$R_{\theta JC}$	20			
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

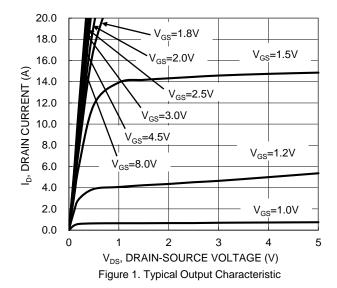
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	12			V	$V_{GS} = 0V, I_{D} = 250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_	_	1.0	μA	V _{DS} = 12V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	0.4		1	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
			17	29		$V_{GS} = 4.5V, I_{D} = 5A$
Static Drain-Source On-Resistance	D	_	20	34	mΩ	$V_{GS} = 2.5V, I_{D} = 4.6A$
Static Drain-Source On-Resistance	Rds(on)	_	24	44	11122	V _{GS} = 1.8V, I _D = 4.1A
		_	30	65		Vgs = 1.5V, ID = 2A
Diode Forward Voltage	VsD	_	0.6	1.2	V	Vgs = 0V, Is = 1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	Ciss	_	914		pF	V 0V V 0V
Output Capacitance	Coss	_	132	_	pF	V _{DS} = 6V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	119	_	pF	1 = 1.0WHZ
Gate Resistance	Rg	_	1.26	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)	0	_	10.5	_	nC	
Total Gate Charge (VGS = 8V)	Qg	_	19.6	_	nC	V 0V 1 0.5A
Gate-Source Charge	Qgs	_	1.2	_	nC	$V_{DS} = 6V, I_{D} = 6.5A$
Gate-Drain Charge	Qgd	_	1.6	_	nC	1
Turn-On Delay Time	tD(ON)	_	5.0	_	ns	
Turn-On Rise Time	t _R	_	10.5		ns	$V_{DD} = 6V, V_{GS} = 4.5V,$
Turn-Off Delay Time	tD(OFF)	_	16.6	_	ns	$R_L = 1.2\Omega$, $R_g = 1\Omega$
Turn-Off Fall Time	t _F	_	4.1	_	ns	

5. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.





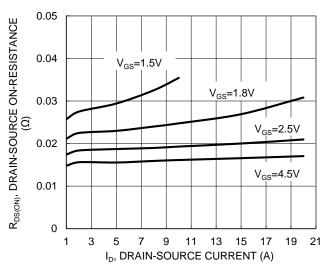


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

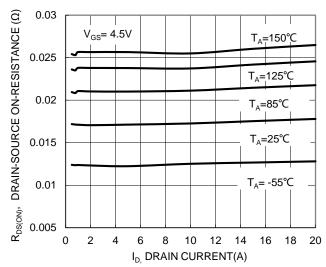
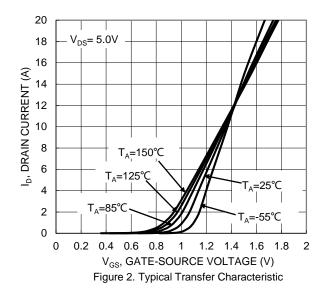
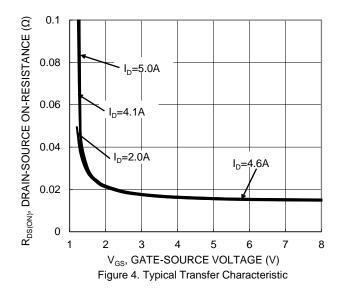


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





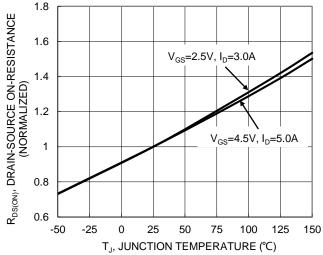


Figure 6. On-Resistance Variation with Temperature



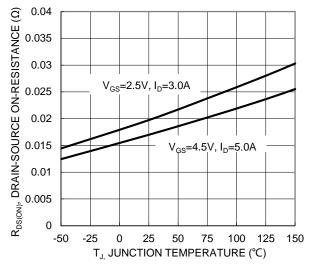


Figure 7. On-Resistance Variation with Temperature

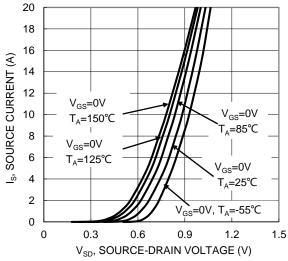
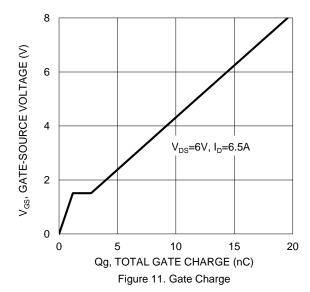
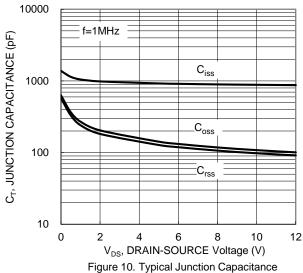


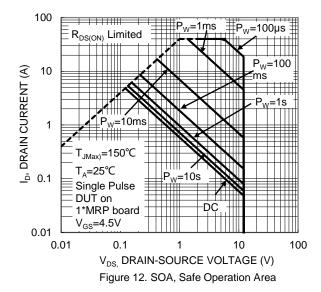
Figure 9. Diode Forward Voltage vs. Current



 $V_{GS(TH)}$, GATE THRESHOLD VOLTAGE (V) 0.9 0.8 0.7 $I_D=1mA$ 0.6 0.5 0.4 $I_{D} = 250 \mu A$ 0.3 0.2 0.1 0 125 -50 -25 25 50 75 100 150 T_J, JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Junction Temperature







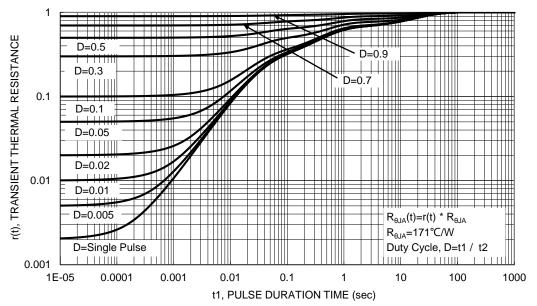


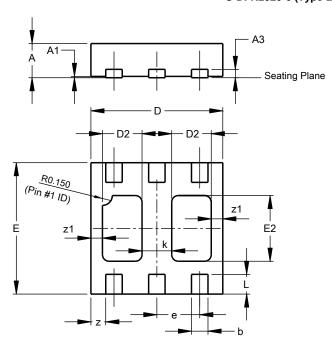
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)

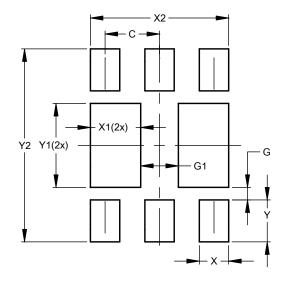


	U-DFN2020-6								
	Type B								
Dim	Min	Max	Тур						
Α	0.545	0.605	0.575						
A1	0.00	0.05	0.02						
A3	-	-	0.13						
b	0.20	0.30	0.25						
D	1.95	2.075	2.00						
D2	0.50	0.70	0.60						
е	-	-	0.65						
E	1.95	2.075	2.00						
E2	0.90	1.10	1.00						
k	-	-	0.45						
L	0.25	0.35	0.30						
Z	-	-	0.225						
z1	-	-	0.175						
All	Dimens	ions in	mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value (in mm)		
	` ,		
С	0.650		
G	0.150		
G1	0.450		
X	0.350		
X1	0.600		
X2	1.650		
Y	0.500		
Y1	1.000		
Y2	2.300		



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